Detlev A Grtzmacher

List of Publications by Citations

301 papers	7,422 citations	43 h-index	72 g-index
322 ext. papers	8,363 ext. citations	4.2 avg, IF	5.44 L-index

#	Paper	IF	Citations
301	Lasing in direct-bandgap GeSn alloy grown on Si. *Nature Photonics*, **2015**, 9, 88-92	33.9	767
300	Intersubband electroluminescence from silicon-based quantum cascade structures. *Science*, **2000**, 290, 2277-80	33.3	229
299	Three-dimensional Si/Ge quantum dot crystals. *Nano Letters*, **2007**, 7, 3150-6	11.5	159
298	Optically Pumped GeSn Microdisk Lasers on Si. *ACS Photonics*, **2016**, 3, 1279-1285	6.3	154
297	Anomalous coiling of SiGe/Si and SiGe/Si/Cr helical nanobelts. *Nano Letters*, **2006**, 6, 1311-7	11.5	141
296	Interface and wetting layer effect on the catalyst-free nucleation and growth of GaN nanowires. *Small*, **2008**, 4, 751-4	11	137
295	Fabrication and characterization of three-dimensional InGaAs/GaAs nanosprings. *Nano Letters*, **2006**, 6, 725-9	11.5	124
294	A new technique for fabricating three-dimensional micro- and nanostructures of various shapes. *Nanotechnology*, **2001**, 12, 399-402	3.4	116
293	Controllable fabrication of SiGe/Si and SiGe/Si/Cr helical nanobelts. *Nanotechnology*, **2005**, 16, 655-663	3.4	113
292	Band engineering and growth of tensile strained Ge/(Si)GeSn heterostructures for tunnel field effect transistors. *Applied Physics Letters*, **2013**, 102, 192103	3.4	112
291	Room-temperature high-frequency transport of dirac fermions in epitaxially grown Sb2Te3- and Bi2Te3-based topological insulators. *Physical Review Letters*, **2014**, 113, 096601	7.4	83
290	Band-gap renormalization and band-filling effects in a homogeneous electron-hole plasma in In0.53Ga0.47As/InP single quantum wells. *Physical Review B*, **1989**, 40, 8087-8090	3.3	82
289	Hall effect measurements on InAs nanowires. *Applied Physics Letters*, **2012**, 101, 152106	3.4	81
288	Impact of nanometer-scale roughness on contact-angle hysteresis and globulin adsorption. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 1715		81
287	Impact of sidewall recombination on the quantum efficiency of dry etched InGaAs/InP semiconductor wires. *Applied Physics Letters*, **1989**, 54, 1552-1554	3.4	80
286	Raman scattering of phonon-plasmon coupled modes in self-assembled GaN nanowires. *Journal of Applied Physics*, **2009**, 105, 123707	2.5	78
285	MBE growth optimization of topological insulator Bi2Te3 films. *Journal of Crystal Growth*, **2011**, 324, 115-118	1.6	75

284	Spin-orbit coupling and phase coherence in InAs nanowires. *Physical Review B*, **2010**, 82,	3.3	74
283	Electroluminescence from strain-compensated Si0.2Ge0.8/Si quantum-cascade structures based on a bound-to-continuum transition. *Applied Physics Letters*, **2002**, 81, 4700-4702	3.4	74
282	Dimer Pairing on the C-Alloyed Si(001) Surface. *Physical Review Letters*, **1999**, 82, 972-975	7.4	72
281	Realization of a vertical topological p-n junction in epitaxial Sb2Te3/Bi2Te3 heterostructures. *Nature Communications*, **2015**, 6, 8816	17.4	70
280	Interface-roughness-induced broadening of intersubband electroluminescence in p-SiGe and n-GaInAs□AlInAs quantum-cascade structures. *Applied Physics Letters*, **2005**, 86, 062113	3.4	68
279	Optical Transitions in Direct-Bandgap Ge1□Snx Alloys. *ACS Photonics*, **2015**, 2, 1539-1545	6.3	67
278	Electronic phase coherence in InAs nanowires. *Nano Letters*, **2011**, 11, 3550-6	11.5	63
277	Freestanding SiGe/Si/Cr and SiGe/Si/SixNy/Cr microtubes. *Applied Physics Letters*, **2004**, 84, 3391-3393	3.4	63
276	Ga-assisted MBE growth of GaAs nanowires using thin HSQ layer. *Journal of Crystal Growth*, **2012**, 353, 39-46	1.6	62
275	Mode of Growth of Ultrathin Topological Insulator Bi2Te3Films on Si (111) Substrates. *Crystal Growth and Design*, **2012**, 12, 6098-6103	3.5	58
274	Molecular beam epitaxy growth of GaAs/InAs core-shell nanowires and fabrication of InAs nanotubes. *Nano Letters*, **2012**, 12, 5559-64	11.5	58
273	Signatures of interaction-induced helical gaps in nanowire quantum point contacts. *Nature Physics*, **2017**, 13, 563-567	16.2	57
272	Reduced Pressure CVD Growth of Ge and Ge1□Snx Alloys. *ECS Journal of Solid State Science and Technology*, **2013**, 2, N99-N102	2	56
271	Effect of Si-doping on InAs nanowire transport and morphology. *Journal of Applied Physics*, **2011**, 110, 053709	2.5	55
270	X-ray nanodiffraction on a single SiGe quantum dot inside a functioning field-effect transistor. *Nano Letters*, **2011**, 11, 2875-80	11.5	55
269	Tensely strained GeSn alloys as optical gain media. *Applied Physics Letters*, **2013**, 103, 192110	3.4	53
268	Self-catalyzed VLS grown InAs nanowires with twinning superlattices. *Nanotechnology*, **2013**, 24, 335601	3.4	52
267	Photon drag effect in (Bi1□Sbx)2Te3 three-dimensional topological insulators. *Physical Review B*, **2016**, 93,	3.3	50

266	Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere. *Applied Physics Letters*, **1993**, 63, 2531-2533	3.4	50
265	Three-dimensional nanosprings for electromechanical sensors. *Sensors and Actuators A: Physical*, **2006**, 130-131, 54-61	3.9	49
264	Advanced GeSn/SiGeSn Group IV Heterostructure Lasers. *Advanced Science*, **2018**, 5, 1700955	13.6	48
263	Suppressing Twin Domains in Molecular Beam Epitaxy Grown Bi2Te3 Topological Insulator Thin Films. *Crystal Growth and Design*, **2015**, 15, 390-394	3.5	48
262	Mode of growth in LP-MOVPE deposition of GaInAs/InP quantum wells. *Journal of Electronic Materials*, **1990**, 19, 471-479	1.9	48
261	Field effect transistor based on single crystalline InSb nanowire. *Journal of Materials Chemistry*, **2011**, 21, 2459		47
260	BiTe is a dual topological insulator. *Nature Communications*, **2017**, 8, 14976	17.4	46
259	Robust surface electronic properties of topological insulators: Bi2Te3 films grown by molecular beam epitaxy. *Applied Physics Letters*, **2011**, 98, 222503	3.4	46
258	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. *Nanotechnology*, **2013**, 24, 085603	3.4	42
257	Effect of growth parameters on the interfacial structure of GaInAs/InP quantum wells. *Journal of Crystal Growth*, **1991**, 107, 537-542	1.6	42
256	SiGeSn growth studies using reduced pressure chemical vapor deposition towards optoelectronic applications. *Thin Solid Films*, **2014**, 557, 183-187	2.2	41
255	Flux periodic magnetoconductance oscillations in GaAs/InAs core/shell nanowires. *Physical Review B*, **2014**, 89,	3.3	40
254	Activation of Zn and Cd acceptors in InP grown by metalorganic vapor phase epitaxy. *Applied Physics Letters*, **1989**, 54, 2411-2413	3.4	40
253	Misfit dislocation free InAs/GaSb core-shell nanowires grown by molecular beam epitaxy. *Nanoscale* , **2015**, 7, 356-64	7.7	39
252	Electronic structure, surface morphology, and topologically protected surface states of Sb2Te3 thin films grown on Si(111). *Journal of Applied Physics*, **2013**, 113, 053706	2.5	39
251	In situ scanning tunneling microscopy study of C-induced Ge quantum dot formation on Si(100). *Applied Physics Letters*, **1999**, 74, 994-996	3.4	39
250	Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence. *Journal of Crystal Growth*, **1991**, 107, 543-548	1.6	38
249	Coexistence of weak localization and a metallic phase in Si/SiGe quantum wells. *Physical Review B*, **2000**, 61, R5082-R5085	3.3	37

248	Ballistic Transport and Exchange Interaction in InAs Nanowire Quantum Point Contacts. *Nano Letters*, **2016**, 16, 3116-23	11.5	37
247	MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. *Journal of Crystal Growth*, **2010**, 312, 635-640	1.6	36
246	Free-standing Si/SiGe micro- and nano-objects. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 23, 280-284	3	36
245	Growth and analysis of quantum well structures. *Journal of Crystal Growth*, **1991**, 107, 520-530	1.6	36
244	Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. *Applied Physics Letters*, **2016**, 108, 061107	3.4	36
243	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. *Nanotechnology*, **2013**, 24, 035203	3.4	35
242	Quantum Transport and Nano Angle-resolved Photoemission Spectroscopy on the Topological Surface States of Single Sb2Te3 Nanowires. *Scientific Reports*, **2016**, 6, 29493	4.9	35
241	Ge quantum dot molecules and crystals: Preparation and properties. *Surface Science*, **2007**, 601, 2787-2791	2.8	34
240	Selective area growth and stencil lithography for in situ fabricated quantum devices. *Nature Nanotechnology*, **2019**, 14, 825-831	28.7	33
239	Spin-polarization limit in Bi2Te3 Dirac cone studied by angle- and spin-resolved photoemission experiments and ab initio calculations. *Physical Review B*, **2013**, 87,	3.3	33
238	Tuning the Dirac point to the Fermi level in the ternary topological insulator (Bi1−xSbx)2Te3. *Applied Physics Letters*, **2015**, 107, 251603	3.4	33
237	SiGeSn Ternaries for Efficient Group IV Heterostructure Light Emitters. *Small*, **2017**, 13, 1603321	11	32
236	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (1 1 1) B using N2 carrier gas. *Journal of Crystal Growth*, **2009**, 311, 3813-3816	1.6	32
235	Magnetoluminescence study of many-body effects in homogeneous quasi-two-dimensional electron-hole plasma in undoped InxGa1-xAs/InP single quantum wells. *Physical Review B*, **1991**, 44, 10680-10688	3.3	32
234	Electrical spin injection into InN semiconductor nanowires. *Nano Letters*, **2012**, 12, 4437-43	11.5	31
233	Nanoscale Near-Field Tomography of Surface States on (BiSb)Te. *Nano Letters*, **2018**, 18, 7515-7523	11.5	31
232	Growth, characterization, and transport properties of ternary (Bi Sb)Te topological insulator layers. *Journal of Physics Condensed Matter*, **2016**, 28, 495501	1.8	30
231	Fabrication and characterization of freestanding Si/Cr micro- and nanospirals. *Microelectronic Engineering*, **2006**, 83, 1237-1240	2.5	30

230	Analysis of the metallic phase of two-dimensional holes in SiGe in terms of temperature dependent screening. *Physical Review Letters*, **2000**, 85, 4357-60	7.4	30
229	Self-organized growth of Ge quantum dots on Si(001) substrates induced by sub-monolayer C coverages. *Nanotechnology*, **1999**, 10, 122-126	3.4	30
228	Diffusion of Zn acceptors during MOVPE of InP. *Journal of Crystal Growth*, **1991**, 108, 449-454	1.6	30
227	Optical properties of very narrow GaInAs/InP quantum wells grown by low-pressure metalorganic vapor phase epitaxy. *Applied Physics Letters*, **1988**, 52, 872-873	3.4	30
226	PN Junctions in Ultrathin Topological Insulator Sb2Te3/Bi2Te3 Heterostructures Grown by Molecular Beam Epitaxy. *Crystal Growth and Design*, **2016**, 16, 2057-2061	3.5	29
225	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. *Journal of Applied Physics*, **2012**, 112, 034316	2.5	29
224	Controlled wurtzite inclusions in self-catalyzed zinc blende III-V semiconductor nanowires. *Journal of Crystal Growth*, **2013**, 378, 506-510	1.6	28
223	Axial strain in GaAs/InAs core-shell nanowires. *Applied Physics Letters*, **2013**, 102, 043109	3.4	28
222	Manipulating InAs nanowires with submicrometer precision. *Review of Scientific Instruments*, **2011**, 82, 113705	1.7	28
221	Nanometer lithography for III-V semiconductor wires using chloromethylated poly-α-methylstyrene resist. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1988**, 6, 2308		28
220	Impact of template variations on shape and arrangement of Si/Ge quantum dot arrays. *Applied Physics Letters*, **2008**, 92, 143102	3.4	27
219	Nucleation of Ge dots on the C-alloyed Si(001) surface. *Physical Review B*, **2002**, 66,	3.3	27
218	Excitons in dense two-dimensional electron-hole magnetoplasmas. *Physical Review B*, **1992**, 46, 12765-12768	3.5	26
217	Resolving ambiguities in nanowire field-effect transistor characterization. *Nanoscale*, **2015**, 7, 18188-97	7.7	25
216	Two-dimensional arrays of self-organized Ge islands obtained by chemical vapor deposition on pre-patterned silicon substrates. *Nanotechnology*, **2007**, 18, 455307	3.4	25
215	Intersubband absorption performed on p-type modulation-doped Si0.2Ge0.8/Si quantum wells grown on Si0.5Ge0.5 pseudosubstrate. *Applied Physics Letters*, **2002**, 80, 3274-3276	3.4	25
214	Formation and ordering effects of C-induced Ge dots grown on Si (001) by molecular beam epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 74, 222-228	3.1	25
213	Crystal Phase Transformation in Self-Assembled InAs Nanowire Junctions on Patterned Si Substrates. *Nano Letters*, **2016**, 16, 1933-41	11.5	24

212	Structural and optical properties of InGaN□GaN nanowire heterostructures grown by molecular beam epitaxy. *Journal of Applied Physics*, **2011**, 109, 014309	2.5	24
211	X-ray diffraction investigation of a three-dimensional Si/SiGe quantum dot crystal. *Physical Review B*, **2009**, 79,	3.3	24
210	Photoluminescence studies of SiGe quantum dot arrays prepared by templated self-assembly. *Europhysics Letters*, **2008**, 84, 67017	1.6	24
209	Adiabatic Edge Channel Transport in a Nanowire Quantum Point Contact Register. *Nano Letters*, **2016**, 16, 4569-75	11.5	23
208	Crystal Phase Selective Growth in GaAs/InAs Core□Shell Nanowires. *Crystal Growth and Design*, **2014**, 14, 1167-1174	3.5	23
207	Broadband transmission masks, gratings and filters for extreme ultraviolet and soft X-ray lithography. *Thin Solid Films*, **2012**, 520, 5080-5085	2.2	23
206	Hall mobility of narrow Si0.2Ge0.8□Si quantum wells on Si0.5Ge0.5 relaxed buffer substrates. *Applied Physics Letters*, **2004**, 84, 2829-2831	3.4	23
205	Photoluminescence study of interdiffusion in In0.53Ga0.47As/InP surface quantum wells. *Applied Physics Letters*, **1992**, 60, 2660-2662	3.4	23
204	Fabrication and optical characterization of quantum wires from semiconductor materials with varying In content. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1989**, 7, 2030		23
203	Magnetotransport studies of □doping layers in MOCVD-grown InP. *Semiconductor Science and Technology*, **1989**, 4, 16-19	1.8	23
202	Electrical resistance of individual defects at a topological insulator surface. *Nature Communications*, **2017**, 8, 15704	17.4	22
201	Three-dimensional phononic nanocrystal composed of ordered quantum dots. *Applied Physics Letters*, **2010**, 96, 123113	3.4	22
200	Ultra flexible SiGe/Si/Cr nanosprings. *Microelectronics Journal*, **2008**, 39, 478-481	1.8	22
199	Nanorobotics for creating NEMS from 3D helical nanostructures. *Journal of Physics: Conference Series*, **2007**, 61, 257-261	0.3	21
198	Magnetotransport in narrow In0.53Ga0.47As/InP wires. *Applied Physics Letters*, **1990**, 57, 1757-1759	3.4	21
197	Nano-light-emitting-diodes based on InGaN mesoscopic structures for energy saving optoelectronics. *Applied Physics Letters*, **2016**, 109, 041103	3.4	21
196	Core□Shell CdTe□TiO2 nanostructured solar cell. *Journal of Materials Chemistry*, **2012**, 22, 10441		20
195	Novel nanostructure architectures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 25, 280-287	3	20

194	Nucleation of Ge quantum dots on the C-alloyed Si(001) surface. *Thin Solid Films*, **2000**, 380, 176-179	2.2	20
193	Opto-electronic characterization of three dimensional topological insulators. *Journal of Applied Physics*, **2016**, 120, 165301	2.5	20
192	Selective area growth of Bi2Te3 and Sb2Te3 topological insulator thin films. *Journal of Crystal Growth*, **2016**, 443, 38-42	1.6	19
191	Crossover from Josephson effect to single interface Andreev reflection in asymmetric superconductor/nanowire junctions. *Nano Letters*, **2014**, 14, 4977-81	11.5	19
190	Electronic transport with dielectric confinement in degenerate InN nanowires. *Nano Letters*, **2012**, 12, 2768-72	11.5	19
189	Domain formation due to surface steps in topological insulator Bi2Te3 thin films grown on Si (111) by molecular beam epitaxy. *Applied Physics Letters*, **2013**, 103, 081902	3.4	19
188	Hot-hole effects in a dilute two-dimensional gas in SiGe. *Europhysics Letters*, **2003**, 61, 499-505	1.6	18
187	. *IEEE Transactions on Electron Devices*, **1992**, 39, 1028-1031	2.9	18
186	Resonance spectroscopy of InGaAs/InP quantum well sub-bands. *Semiconductor Science and Technology*, **1988**, 3, 797-801	1.8	18
185	MBE growth of Al/InAs and Nb/InAs superconducting hybrid nanowire structures. *Nanoscale*, **2017**, 9, 16735-16741	7.7	17
184	Topography and structure of ultrathin topological insulator Sb2Te3 films on Si(111) grown by means of molecular beam epitaxy. *Journal of Crystal Growth*, **2016**, 453, 158-162	1.6	17
183	Si substrate preparation for the VS and VLS growth of InAs nanowires. *Physica Status Solidi - Rapid Research Letters*, **2013**, 7, 840-844	2.5	17
182	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. *Applied Physics Letters*, **2010**, 97, 173505	3.4	17
181	Evolution and stability of ordered SiGe islands grown on patterned Si(100) substrates. *Journal of Applied Physics*, **2009**, 105, 122405	2.5	17
180	In situinvestigations of Si and Ge interdiffusion in Ge-rich Si/SiGe multilayers using x-ray scattering. *Semiconductor Science and Technology*, **2007**, 22, 447-453	1.8	17
179	Size control of carbon-induced Ge quantum dots. *Applied Physics Letters*, **2000**, 77, 3218-3220	3.4	17
178	Selective growth of Si/SiGe resonant tunneling diodes by atmospheric pressure chemical vapor deposition. *Applied Physics Letters*, **1992**, 61, 2872-2874	3.4	17
177	Infrared/terahertz spectra of the photogalvanic effect in (Bi,Sb)Te based three-dimensional topological insulators. *Physical Review Materials*, **2018**, 2,	3.2	17

176	Observation of valence-band Landau-level mixing by resonant magnetotunneling. *Physical Review B* , **1993**, 47, 16036-16039	3.3	16
175	Controlled uniform growth of GaInAsP/InP structures for laser application on 2 inch wafers by LP-MOVPE at 20 mbar. *Journal of Crystal Growth*, **1988**, 93, 285-291	1.6	16
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173	Giant magnetoconductance oscillations in hybrid superconductor-semiconductor core/shell nanowire devices. *Nano Letters*, **2014**, 14, 6269-74	11.5	15
172	Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. *Journal of Crystal Growth*, **2013**, 370, 336-341	1.6	15
171	Coherent ultrafast spin-dynamics probed in three dimensional topological insulators. *Scientific Reports*, **2015**, 5, 15304	4.9	15
170	Enhanced Raman Scattering of Ultramarine on Au-coated Ge/Si-nanostructures. *Plasmonics*, **2011**, 6, 413-418	2.4	15
169	Tensile strained SiGe quantum well infrared photodetectors based on a light-hole ground state. *Applied Physics Letters*, **2011**, 98, 211106	3.4	15
168	Cost estimate of electricity produced by TPV. *Semiconductor Science and Technology*, **2003**, 18, S254-S261	1.8	15
167	Band gap and band alignment of strain reduced Si/Si1□□GexCy multiple quantum well structures obtained by photoluminescence measurements. *Applied Physics Letters*, **1998**, 73, 1257-1259	3.4	15
166	Anomalous magnetoresistance peak in quantum wires: Evidence for boundary-scattering mechanisms. *Physical Review B*, **1993**, 47, 6524-6528	3.3	15
165	Enhanced light scattering of the forbidden longitudinal optical phonon mode studied by micro-Raman spectroscopy on single InN nanowires. *Nanotechnology*, **2010**, 21, 315702	3.4	14
164	Phase coherent transport in InSb nanowires. *Applied Physics Letters*, **2012**, 101, 082103	3.4	14
163	Directed batch assembly of three-dimensional helical nanobelts through angular winding and electroplating. *Nanotechnology*, **2007**, 18, 055304	3.4	14
162	Intersubband absorption of strain-compensated Si1□Gex valence-band quantum wells with 0.7?x?0.85. *Journal of Applied Physics*, **2005**, 98, 044501	2.5	14
161	In-plane valence-band nonparabolicity and anisotropy in strained Si-Ge quantum wells. *Physical Review B*, **1993**, 48, 15112-15115	3.3	14
160	In0.53Ga0.47As/InP quantum wires: Fabrication and magnetotransport studies. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1990**, 8, 1353		14
159	LP-MOCVD growth and characterization of undoped and modulation doped GaInAsP/InP and GaInAs/InP multi quantum wells. *Journal of Crystal Growth*, **1988**, 93, 382-388	1.6	14

158	Generation of circularly polarized radiation from a compact plasma-based extreme ultraviolet light source for tabletop X-ray magnetic circular dichroism studies. *Review of Scientific Instruments*, **2014**, 85, 103110	1.7	13
157	Monolithic Integration of Ultrafast Photodetector and MESFET in the GaN Material System. *IEEE Photonics Technology Letters*, **2011**, 23, 1189-1191	2.2	13
156	SiGe quantum well infrared photodetectors on pseudosubstrate. *Applied Physics Letters*, **2009**, 94, 081115	3.4	13
155	Sensitivity Enhancement of Metal–Semiconductor–Metal Photodetectors on Low-Temperature-Grown GaAs Using Alloyed Contacts. *IEEE Photonics Technology Letters*, **2008**, 20, 1054-1056	2.2	13
154	Shape and composition change of Ge dots due to Si capping. *Applied Surface Science*, **2004**, 224, 139-142	6.7	13
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152	Single-hole transistor in a p-Si/SiGe quantum well. *Applied Physics Letters*, **2001**, 78, 341-343	3.4	13
151	Optical and structural properties of MOVPE grown GaxIn1−xAs/InP strained multiple quantum well atructures. *Journal of Electronic Materials*, **1992**, 21, 293-298	1.9	13
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149	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. *Applied Physics Letters*, **2012**, 100, 042103	3.4	12
148	Direct monitoring of the excited state population in biased SiGe valence band quantum wells by femtosecond resolved photocurrent experiments. *Applied Physics Letters*, **2006**, 89, 211111	3.4	12
147	In situ disentangling surface state transport channels of a topological insulator thin film by gating. *Npj Quantum Materials*, **2018**, 3,	5	12
146	Non-uniform distribution of induced strain in a gate-recessed AlGaN/GaN structure evaluated by micro-PL measurements. *Semiconductor Science and Technology*, **2012**, 27, 105008	1.8	11
145	Templated self-organization of SiGe quantum structures for nanoelectronics. *Materials Science and Engineering C*, **2007**, 27, 947-953	8.3	11
144	Fabrication of SiGe/Si/Cr bent cantilevers based on self-rolling of epitaxial films. *Microelectronic Engineering*, **2003**, 67-68, 595-601	2.5	11
143	Photoluminescence of carbon-induced Ge islands in silicon. *Thin Solid Films*, **2000**, 380, 246-248	2.2	11
142	Boron redistribution in arsenic-implanted silicon and short-channel effects in metal–oxide–semiconductor field effect transistors. *Applied Physics Letters*, **1992**, 61, 3038-3040	3.4	11
141	Properties of the two-dimensional electron gas in modulation-doped GaInAs(P)/InP structures grown by low-pressure metalorganic vapor-phase epitaxy. *Journal of Applied Physics*, **1989**, 66, 697-703	2.5	11

140	. *IEEE Transactions on Microwave Theory and Techniques*, **1989**, 37, 2093-2098	4.1	11
139	Optical properties of GaInAs/InP multi-quantum wells grown by low-pressure MOVPE. *Semiconductor Science and Technology*, **1990**, 5, 222-228	1.8	11
138	Electron-hole transition energies and atomic steps at the interfaces of thin InGaAs/InP quantum wells. *Applied Physics Letters*, **1990**, 56, 632-634	3.4	11
137	Electron Interference in Hall Effect Measurements on GaAs/InAs Core/Shell Nanowires. *Nano Letters*, **2017**, 17, 128-135	11.5	10
136	Chalcogenide-based van der Waals epitaxy: Interface conductivity of tellurium on Si(111). *Physical Review B*, **2017**, 96,	3.3	10
135	Femtosecond and highly sensitive GaAs metal□semiconductor□metal photodetectors grown on aluminum mirrors/pseudo-substrates. *Semiconductor Science and Technology*, **2010**, 25, 075001	1.8	10
134	Integration of MOSFETs with SiGe dots as stressor material. *Solid-State Electronics*, **2011**, 60, 75-83	1.7	10
133	Subpicosecond electron-hole recombination time and terahertz-bandwidth photoresponse in freestanding GaAs epitaxial mesoscopic structures. *Applied Physics Letters*, **2012**, 101, 031111	3.4	10
132	Absorption measurement of strained SiGe nanostructures deposited by UHV-CVD. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 16, 481-488	3	10
131	Stencil lithography of superconducting contacts on MBE-grown topological insulator thin films. *Journal of Crystal Growth*, **2017**, 477, 183-187	1.6	9
130	Angle-dependent magnetotransport in GaAs/InAs core/shell nanowires. *Scientific Reports*, **2016**, 6, 24573	4.9	9
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